

EE 434

Lecture 31

Device Sizing of Static CMOS Circuits

Quiz: If a CMOS inverter with
 $w_n = 2\mu$, $w_p = 4\mu$, $L_n = L_p = L_a$ is designed
in a process with $\mu\tau_{ox} = 10^{-4}$, $V_{TN} = |V_{TP}| = 1V$,
 $\gamma = 0$ and $\lambda = 0$, what will the output voltage
be when both devices are in saturation?
Assume $V_{DD} = 5V$

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Solution:

When M_1 & M_2 are in saturation,

V_0 is indeterminate since

$$V_{in} = \frac{V_{TN} + (V_{DD} + V_{TP}) \sqrt{\frac{\mu_p}{\mu_n} \frac{W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{\mu_p}{\mu_n} \frac{W_2 L_1}{W_1 L_2}}}$$

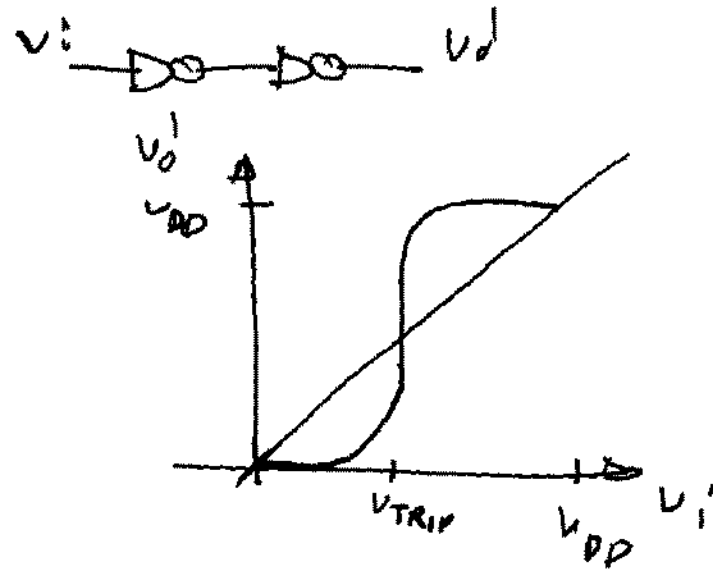
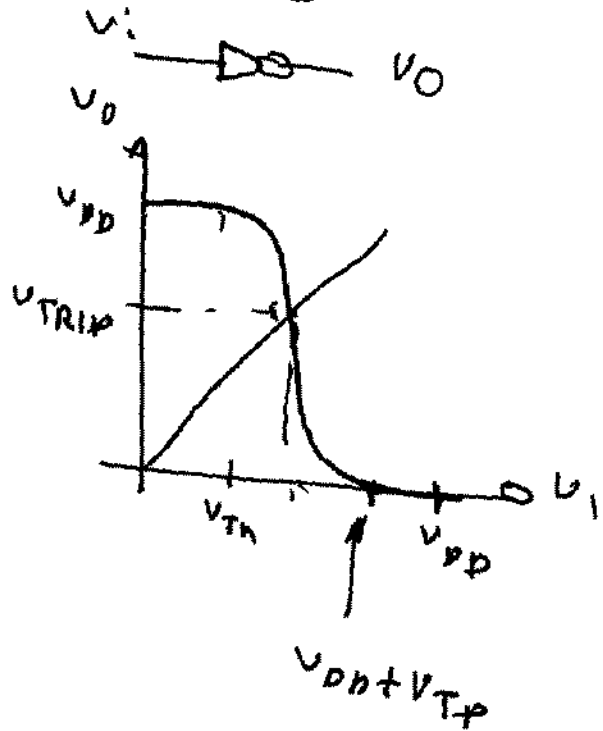
Review from Last Time:

- Elmore delay model provides quick approximate delay prediction
- Inverter and Inverter Pair Transfer Characteristics both provide V_{TRIP} from $X_0 = X_i$ line
- DC transfer characteristics of inverter can be systematically obtained

Observations

Inverters have devices that ideally never operate in sat.

(Ideally one is in CO and other in triode)



$$V_H = v_{DD}$$

$$V_L = 0$$

$$V_{TRIP} = \frac{V_{TH} + (v_{DD} + V_{TP})\sqrt{\gamma}}{1 + \sqrt{\gamma}}$$

$$\sqrt{\gamma} = \sqrt{\frac{\mu_p w_2 L_1}{\mu_n w_1 L_2}}$$

What is V_{TRIP} for the static CMOS Inverter?

In a typical process

$$V_{Tn} \approx .2V_{DD}$$

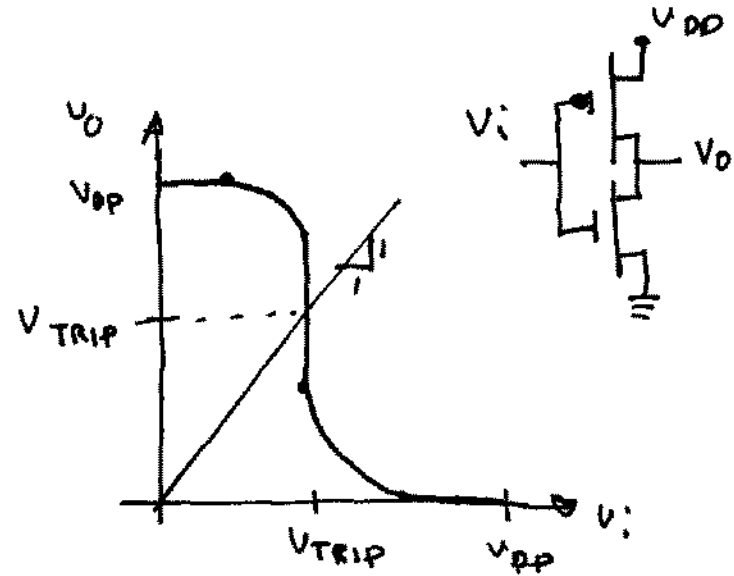
$$|V_{Tp}| \approx .2V_{DD}$$

$$\mu_p \approx 3^{-1} \mu_n$$

$$\sqrt{\frac{1}{3} \frac{\mu_2 k_1}{\mu_1 k_2}}$$

$$V_{TRIP} = \frac{.2V_{DD} + (V_{DD} - .2V_{DD})\sqrt{\quad}}{1 + \sqrt{\quad}}$$

$$= V_{DD} \left(\frac{.2 + .8\sqrt{\quad}}{1 + \sqrt{\quad}} \right)$$



* V_{TRIP} for minimum sized devices:

$$\text{If } w_1 = w_2 = L_1 = L_2 = L_{min}$$

$$V_{TRIP} = V_{DD} \left(\frac{.2 + .8 \sqrt{1/3}}{1 + \sqrt{1/3}} \right) = .42 V_{DD}$$

* V_{TRIP} for $w_2/w_1 = \frac{\mu_n}{\mu_p}$

$$\text{If } w_1 = \cancel{L_1} = L_1 = L_2 = L_{min}$$

$$w_2 = 3w_1$$

$$\sqrt{\frac{1}{3} \frac{w_2 L_1}{L_2 w_1}} = 1$$

$$V_{TRIP} = V_{DD} \left(\frac{.2 + .8}{1 + 1} \right) = \frac{V_{DD}}{2}$$

- Device sizing substantially affects V_{TRIP}

Device Sizing Strategies

1) Minimum Sized Devices

$$V_H = V_{DD}, V_L = 0 \quad \text{☺}$$

$$V_{TRIP} \approx 0.4 V_{DD} \quad \text{☹}$$

2)
$$V_{TRIP} = \frac{V_{DD}}{2}$$

From previous example, observe that

$$\frac{\mu_p}{\mu_n} \frac{W_2 L_1}{L_2 W_1} = 1$$

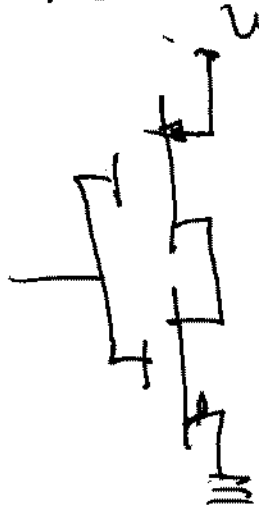
Thus

$\begin{aligned} L_1 &= L_2 = L_{min} \\ W_1 &= W_{min} \\ W_2 &= 3W_{min} \end{aligned}$

3) Equal t_{HL} & t_{LH}

- slow in the timing
- pull up time is slow when minimum sized devices are used

For equal t_{rise} and t_{fall}



$$R_{PD} = R_{PU}$$

$$\therefore \frac{L_1}{\mu_n C_{ox} W_1 (V_{DD} - V_{TH})} = \frac{L_2}{\mu_p C_{ox} W_2 (V_{DD} + V_{TP})}$$

$$t_{HL} = C_{REF} R_{PD}$$

$$t_{LH} = C_{REF} R_{PU}$$

$$\frac{L_1}{W_1} \frac{W_2}{L_2} = \frac{\mu_n}{\mu_p} \left(\frac{V_{DD} - V_{TH}}{V_{DD} + V_{TP}} \right)$$

$$W_2 = W_1 \left(\frac{\mu_n}{\mu_p} \right) \left(\frac{V_{DD} - V_{TH}}{V_{DD} + V_{TP}} \right)$$

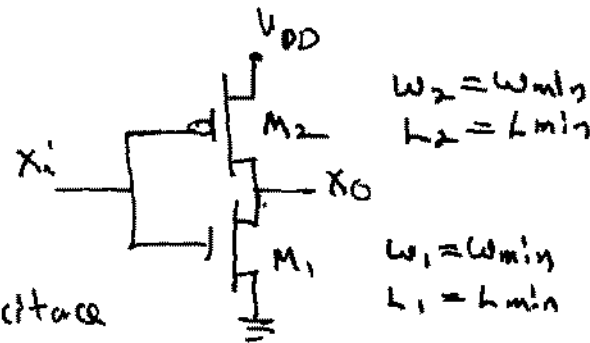
If $V_{TH} = .2V_{DD}$, $V_{TP} = -.2V_{DD}$

$$W_2 = \left(\frac{\mu_n}{\mu_p} \right) W_1$$

Note: with these threshold choices, $V_{TRIP} = V_{DD}/2$ sizing criterion is identical to equal rise/fall criteria. 😊

How does the total delay for the minimum sized inverter compare to that of the equal rise/fall time inverter?

Case I. minimum sized



Define C^* to be the input capacitance to this inverter. \therefore

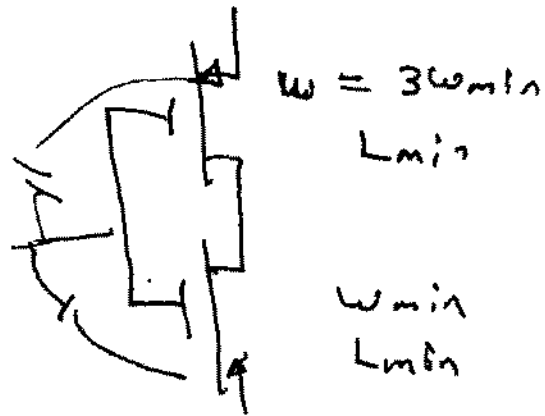
$$C^* = 2 C_{ox} W_{min} L_{min}$$

$$R_{pd}^* = \frac{L_{min}}{\mu_n C_{ox} W_{min} (V_{DD} - V_{Tn})}$$

$$R_{pu}^* = 3 R_{pd}^*$$

$$\begin{aligned} \therefore t_{HL} + t_{LH} &= R_{pd}^* C^* + R_{pu}^* C^* \\ &= R_{pd}^* C^* + 3 R_{pd}^* C^* \\ &= 4 R_{pd}^* C^* \end{aligned}$$

Case 2. Equal Rise & Fall time.



$$C_{REF} = C_{ox} W_{min} L_{min} + C_{ox} 3 W_{min} L_{min}$$

$$= 4 C_{ox} W_{min} L_{min}$$

$$t_{HL} = R_{PD} C_{REF}$$

$$t_{HL} + t_{LH} = 2 R_{PD} C_{REF}$$

$$= 2 R_{PD} 4 C_{ox} W_{min} L_{min}$$

$$= 4 R_{PD}^* C_{REF}^*$$

\therefore speed is identical!

There is no speed improvement with the equal rise/fall time sizing but the total switched capacitance has doubled and the area is modestly larger.